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| INFORMATION DISCLOSURE CITATION PTO-1449 | | Customer Number 26615 | ATTORNEY'S DKT No. H1491 APPLICANT(S) Bin Yu et al. FILING DATE September 3, 2003 | APPLICATION No. Unassigned 10,653,234 GROUP Unassigned 2818 | | |
| U.S. PATENT DOCUMENTS | | | | | | |
| EXAMINER'S INITIALS | PATENT NO. | DATE | NAME | CLASS | SUBCLASS | FILING DATE |
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| FOREIGN PATENT DOCUMENTS | | | | | | |
| EXAMINER'S INITIALS | PATENT NO. | DATE | COUNTRY | CLASS | SUBCLASS | Translation Yes No |
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| OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) | | | | | | |
| <i>dhc</i> | Digh Hisamoto et al.: "FinFET - A Self-Aligned Double-Gate MOSFET Scalable to 20 nm," IEEE Transactions on Electron Devices, Vol. 47, No. 12, December 2000, pages 2320-2325. | | | | | |
| <i>dhc</i> | Yang-Kyu Choi et al.: "Sub-20nm CMOS Fin FET Technologies," 2001 IEEE, IEDM, pages 421-424. | | | | | |
| <i>dhc</i> | Xuejue Huang et al.: "Sub-50 nm P-Channel Fin FET," IEEE Transactions on Electron Devices, Vol. 48, No. 5, May 2001, pages 880-886. | | | | | |
| <i>dhc</i> | Yang-Kyu Choi et al.: "Nanoscale CMOS Spacer FinFET for the Terabit Era," IEEE Electron Device Letters, Vol. 23, No. 1, January 2002, pages 25-27. | | | | | |
| <i>dhc</i> | Xuejue Huang et al.: "Sub 50-nm FinFET: PMOS," 1999 IEEE, IEDM, pages 67-70. | | | | | |
| <i>dhc</i> | Co-pending U.S. Patent Application Serial No. 10/632,965, filed August 4, 2003, entitled: "Semiconductor Device Having A Thin Fin And Raised Source/Drain Areas," Haihong Wang et al.; 18 page specification and 19 sheets of drawings. | | | | | |
| EXAMINER | | | DATE CONSIDERED | | | |
| <i>[Signature]</i> | | | <i>03/22/05</i> | | | |

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).